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CERTIFICATE OF TRANSMISSION

July 30, 2002

Atty Docket No.:	JCLA6974
Appl. No.:	09/930,847
Filing Date:	August, 14, 2001
Pages:	Cover + 10

BY FACSIMILE ONLY

Fax No.: 703-872-9318
Attention: Examiner LEWIS, MONICA
Group Unit: 2822
From: Jiawei Huang, Reg. No. 43,330
MESSAGE: Enclosed is an Amendment in 10 pages.

Sir:

I hereby certify that this correspondence is being facsimile transmitted to the Patent and Trademark Office on **July 30, 2002** at the above indicated fax number.

Sign by: M. Chang
Michelle Chang

#7/Arnett B. 8/2/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:		)
Application No.:	09/930,847	)
Filed:	August 14, 2001	)
For:	Thin Film Transistor having a Reduced Source/Drain Resistance (as Amended)	)
Applicant:	Po-Sheng Shih	)
Examiner:	Monica Lewis	)
Art Unit	2822	)

AMENDMENT

Assistant Commissioner of Patents and Trademarks
Washington, DC 20231

Sir:

In response to the Office Action dated May 8, 2002, please enter the following amendments and consider the following remarks.

IN THE TITLE

Please substitute the following clean copy Title for the pending Title.

--THIN FILM TRANSISTOR HAVING A
REDUCED SOURCE/DRAIN RESISTANCE--

IN THE ABSTRACT

Please substitute the following clean copy text abstract for the pending abstract.

--A structure of a thin film transistor having a reduced source/drain resistance is disclosed. The thin film transistor comprises an ultra thin polysilicon layer over a substrate, a gate structure that includes a gate layer, a gate oxide layer between the gate layer and the ultra thin polysilicon layer and a spacer on each sidewall of the gate layer, and a conductive layer over the ultra thin polysilicon layer and the gate layer adjacent to the spacers. A conductive layer comprising a low resistance material is disposed over the gate layer, and over the ultra thin polysilicon layer

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